

DT04 Rec'd PCT/PTO 23 JUN 2004

PTO/SB/08A-8 (04-03)

Approved for use through 04/30/2003. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for Form 1449/PTO		Complete if Known 107500268	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>		Application Number	Unassigned
		Filing Date	June 23, 2004
		First Named Inventor	ANDO et al.
		Art Unit	Unassigned 1733
		Examiner Name	Unassigned Hitisheh
Sheet	1	of	1
		Attorney Docket Number 92372	

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No.*	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Paragraphs or Relevant Figures Appear	T#
		Country Code-Number-Kind Code* (if known)				
F.H.	JP 07201874		08/04/1995	NEC Corp.		Abstract
F.H.	EP 0 889 510		01/07/1999	Adachi et al.		Yes
F.H.	JP 09194294		07/29/1997	Sumitomo Sitix Corp.		Abstract
SH.	EP 1 035 235		09/13/2000	Tamatsuka et al.		Yes

OTHER ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Case No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
F/H		Adachi, et al.; "Reduction of Grown-In Defects by High Temperature Annealing," <i>Journal of The Electrochemical Society</i> , Vol. 147 (1), pp. 350-353, 2000.	
F/H		Umeno et al.; "Dependence of Grown-In Defect Behavior on Oxygen Concentration in Czochralski Silicon Crystals," <i>Jpn. J. Appl. Phys.</i> , Vol. 38, Pt. 1, No. 10, pp. 5725-5730, 1999.	
F/H		Wijaranakula et al.; "Effect of high-temperature annealing on the dissolution of the D-defects in n-type Czochralski silicon," <i>Appl. Phys. Lett.</i> , Vol. 64 (8), pp. 1030-1032, 21 February 1994.	

Examiner Signature	D. Miller	Date Considered	8/2/2096
-----------------------	-----------	--------------------	----------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²See Kind Codes of USPTO Patent Documents at www.uspto.gov or MPEP 501.04. "Enter Office that issued the document, by the two-letter code (WIPO Standard ST_3). For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document." Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST_16 if possible. ³Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231.